

**40V COMPLEMENTARY MEDIUM POWER TRANSISTOR IN SOT26**

**Features**

- NPN + PNP Combination
- $BV_{CEO} > 40$  (-40)V
- $BV_{ECO} > 6$  (-3)V
- $I_{CM} = 9$  (-9)A Peak Pulse Current
- $V_{CE(sat)} < 60$  (-90)mV @ 1A
- $R_{CE(sat)} = 38$  (58)m $\Omega$
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Description**

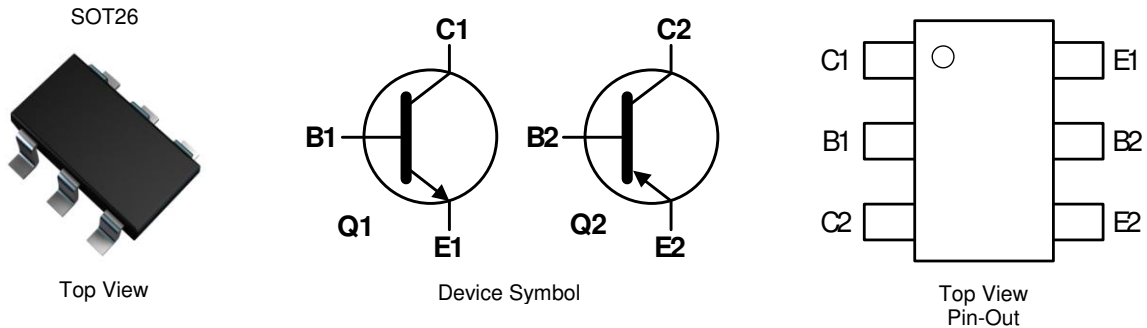
Advanced process capability is used to achieve this high performance device. Combining NPN and PNP transistors in the SOT26 package provides a compact solution for the intended applications.

**Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208③
- Weight: 0.015 grams (Approximate)

**Applications**

- MOSFET and IGBT Gate Driving
- Motor Drive

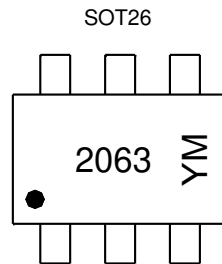


**Ordering Information** (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTC2063E6TA	2063	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See <http://www.diodes.com/> for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
  3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com>.

**Marking Information**



2063 = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: C = 2015)  
 M or  $\bar{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	C	D	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Absolute Maximum Ratings – Q1 (NPN Transistor)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	130	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Collector Voltage (Reverse blocking)	V <sub>ECO</sub>	6	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	I <sub>C</sub>	3.5	A
Peak Pulsed Collector Current	I <sub>CM</sub>	9	A
Base Current	I <sub>B</sub>	1	A

**Absolute Maximum Ratings – Q2 (PNP Transistor)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-45	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Collector Voltage (Reverse blocking)	V <sub>ECO</sub>	-3	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	I <sub>C</sub>	-3	A
Peak Pulsed Collector Current	I <sub>CM</sub>	-9	A
Base Current	I <sub>B</sub>	-1	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

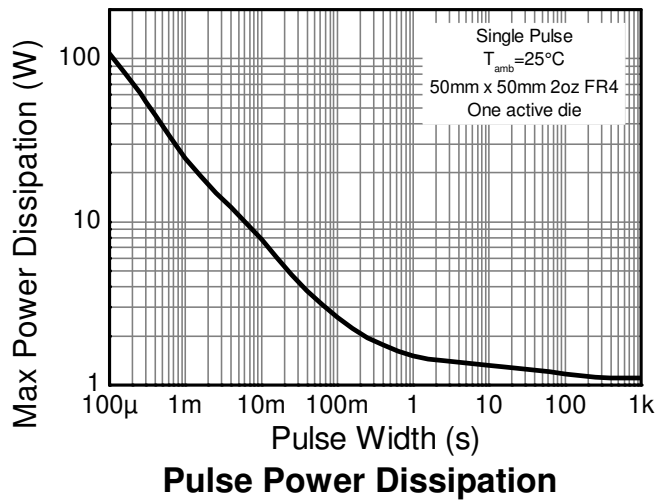
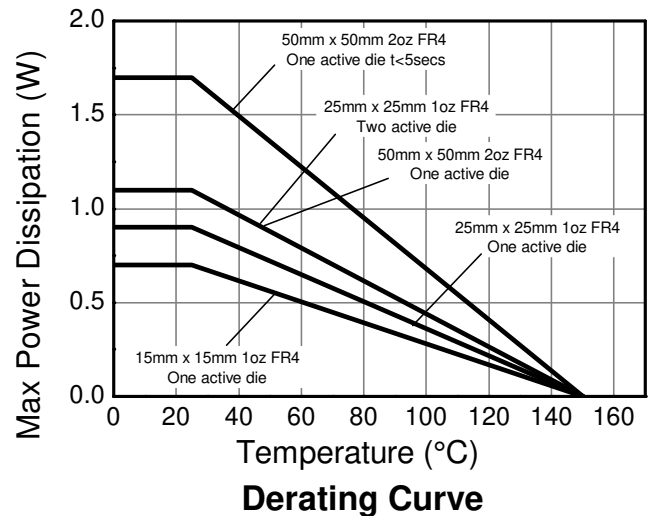
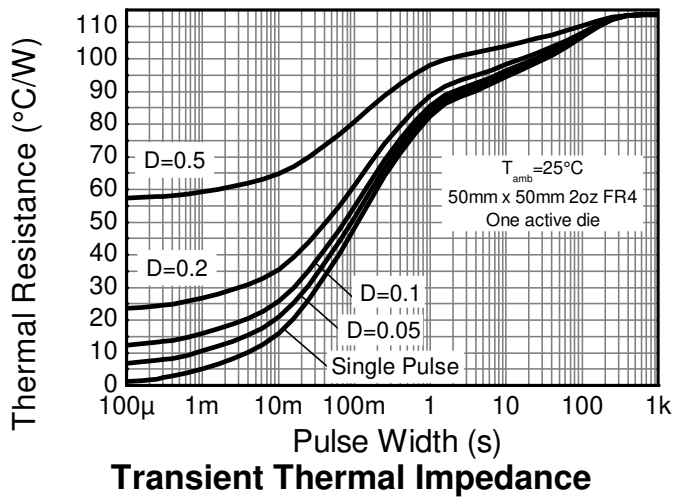
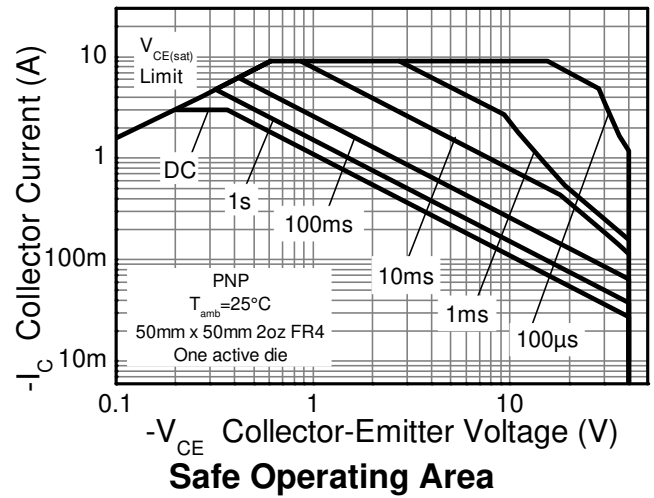
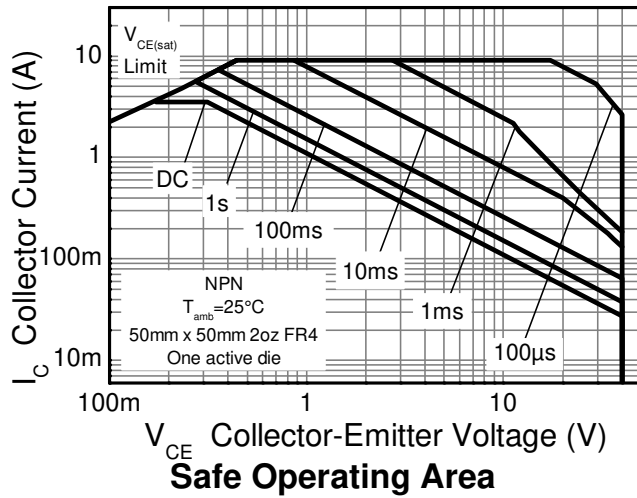
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P <sub>D</sub>	(Notes 5 & 9)	0.7
		(Notes 6 & 9)	5.6
		(Notes 6 & 10)	0.9
		(Notes 7 & 9)	7.2
		(Notes 8 & 9)	1.1
		(Notes 8 & 9)	8.8
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	(Notes 5 & 9)	1.1
		(Notes 6 & 9)	8.8
		(Notes 6 & 10)	1.1
		(Notes 7 & 9)	8.8
		(Notes 8 & 9)	1.7
Thermal Resistance, Junction to Lead	R <sub>θJL</sub>	13.6	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ESD Ratings** (Note 12)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device surface mounted on 15mm x 15mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Same as Note (5), except the device is surface mounted on 25mm x 25mm 1oz copper.
  - Same as Note (5), except the device is surface mounted on 50mm x 50mm 2oz copper.
  - Same as Note (7), except the device is measured at t < 5 seconds.
  - For device with one active die, both collectors attached to a common heatsink.
  - For device with two active dice running at equal power, split heatsink 50% to each collector.
  - Thermal resistance from junction to solder-point (at the end of the collector lead).
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Thermal Characteristics and Derating Information**



**Electrical Characteristics – Q1 (NPN Transistor)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	130	170	—	V	I <sub>C</sub> = 100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage (Note 13)	BV <sub>CEO</sub>	40	63	—	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.3	—	V	I <sub>E</sub> = 100μA, I <sub>C</sub> = 0
Emitter-Collector Breakdown Voltage (reverse blocking)	BV <sub>ECX</sub>	6	7.4	—	V	I <sub>E</sub> = 100μA, R <sub>BC</sub> < 1kΩ or 0.25V > V <sub>BC</sub> > -0.25V
Emitter-Collector Breakdown Voltage (base open)	BV <sub>ECC</sub>	6	7.4	—	V	I <sub>E</sub> = 100μA
Collector Cutoff Current	I <sub>CBO</sub>	—	<1	50	nA	V <sub>CB</sub> = 100V
Collector Cutoff Current	I <sub>EBO</sub>	—	<1	50	nA	V <sub>CB</sub> = 100V, T <sub>A</sub> = +100°C
Collector Cutoff Current	I <sub>EBO</sub>	—	<1	50	nA	V <sub>EB</sub> = 5.6V
<b>ON CHARACTERISTICS (Note 13)</b>						
DC Current Gain	h <sub>FE</sub>	300 280 40	450 400 60	900	—	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 2V I <sub>C</sub> = 1.0A, V <sub>CE</sub> = 2V I <sub>C</sub> = 3.5A, V <sub>CE</sub> = 2V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	50 85 150 135	60 110 220 195	mV	I <sub>C</sub> = 1.0A, I <sub>B</sub> = 100mA I <sub>C</sub> = 1.0A, I <sub>B</sub> = 20mA I <sub>C</sub> = 2.0A, I <sub>B</sub> = 40mA I <sub>C</sub> = 3.5A, I <sub>B</sub> = 350mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	—	960	1,050	mV	I <sub>C</sub> = 3.5A, I <sub>B</sub> = 350mA
Base-Emitter Turn-On Voltage	V <sub>BE(on)</sub>	—	860	950	mV	I <sub>C</sub> = 3.5A, V <sub>CE</sub> = 2V
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Output Capacitance	C <sub>obo</sub>	—	12	20	pF	V <sub>CB</sub> = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f <sub>T</sub>	—	190	—	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 50mA, f = 100MHz
Delay Time	t <sub>d</sub>	—	64	—	ns	V <sub>CC</sub> = 10V, I <sub>C</sub> = 1A, I <sub>B1</sub> = I <sub>B2</sub> = 10mA
Rise Time	t <sub>r</sub>	—	108	—	ns	
Storage Time	t <sub>s</sub>	—	428	—	ns	
Fall Time	t <sub>f</sub>	—	130	—	ns	

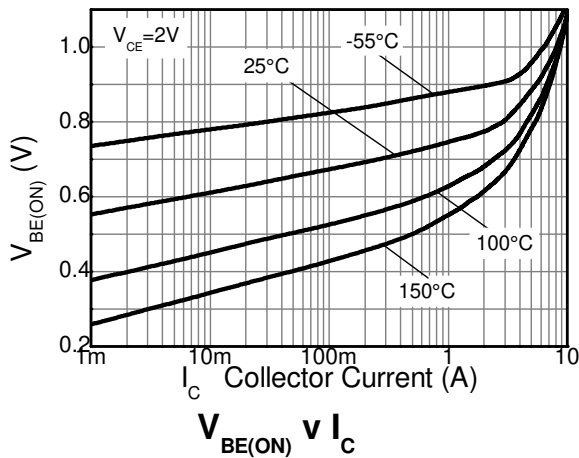
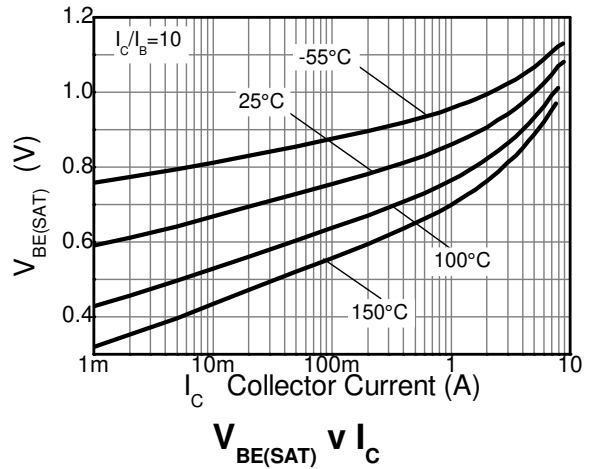
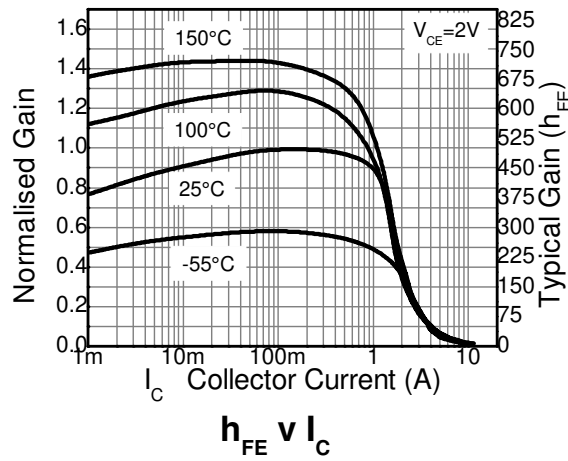
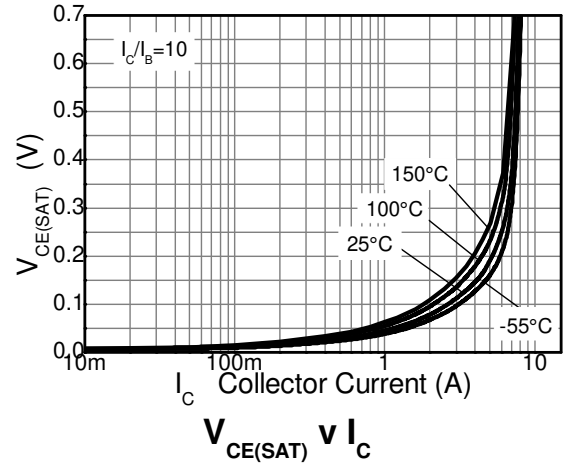
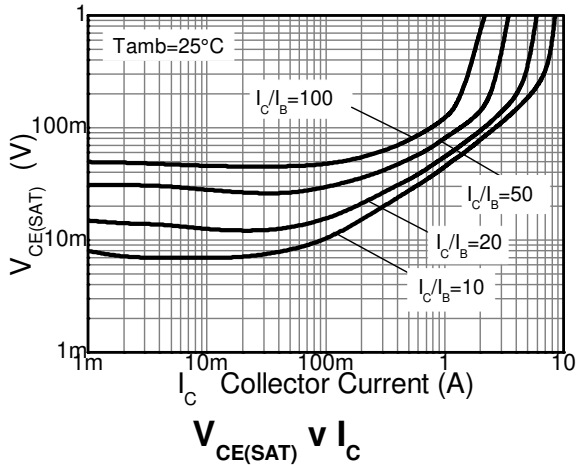
Note: 13. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

**Electrical Characteristics – Q2 (PNP Transistor)** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

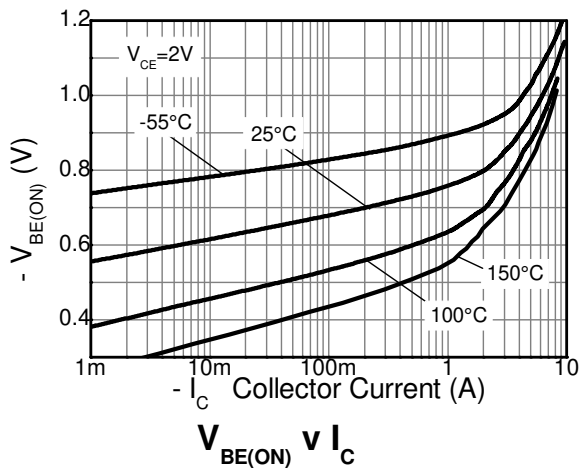
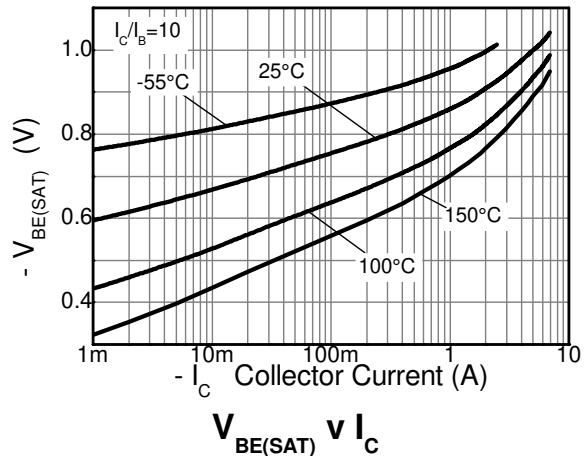
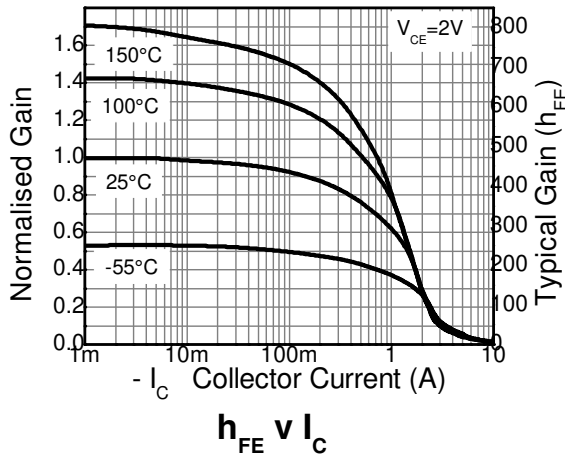
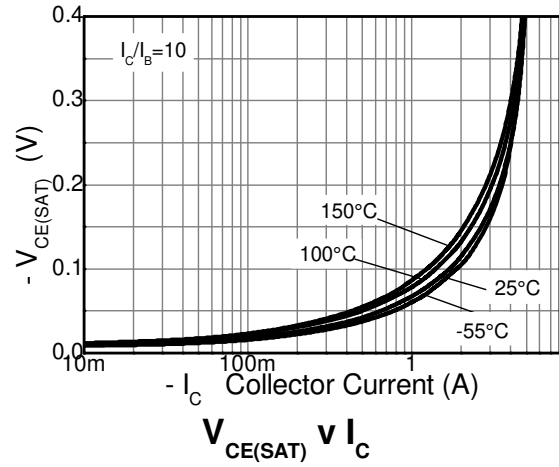
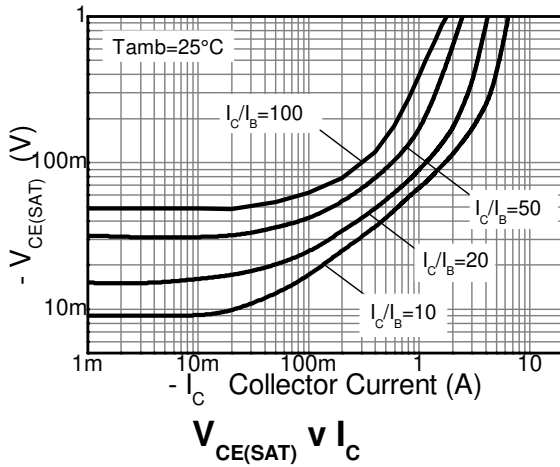
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	$BV_{CBO}$	-45	-80	—	V	$I_C = -100\mu\text{A}$ , $I_E = 0$
Collector-Emitter Breakdown Voltage (Note 14)	$BV_{CEO}$	-40	-65	—	V	$I_C = -10\text{mA}$ , $I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-7	-8.3	—	V	$I_E = -100\mu\text{A}$ , $I_C = 0$
Emitter-Collector Breakdown Voltage (reverse blocking)	$BV_{ECX}$	-6	-7.4	—	V	$-I_E = 100\mu\text{A}$ , $R_{BC} < 1\text{k}\Omega$ or $0.25\text{V} < V_{BC} < -0.25\text{V}$
Emitter-Collector Breakdown Voltage (base open)	$BV_{ECO}$	-3	-8.7	—	V	$I_E = -100\mu\text{A}$
Collector Cutoff Current	$I_{CBO}$	—	<1	-50	nA	$V_{CB} = -36\text{V}$
Collector Cutoff Current	$I_{EBO}$	—	<1	-50	nA	$V_{CB} = -36\text{V}$ , $T_A = +100^\circ\text{C}$
Collector Cutoff Current	$I_{EBO}$	—	<1	-50	nA	$V_{EB} = -5.6\text{V}$
<b>ON CHARACTERISTICS (Note 14)</b>						
DC Current Gain	$h_{FE}$	300 200 20	450 280 50	900 — —	—	$I_C = -10\text{mA}$ , $V_{CE} = -2\text{V}$ $I_C = -1.0\text{A}$ , $V_{CE} = -2\text{V}$ $I_C = -3.0\text{A}$ , $V_{CE} = -2\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	— — —	-70 -195 -175	-90 -290 -260	mV	$I_C = -1.0\text{A}$ , $I_B = -100\text{mA}$ $I_C = -1.0\text{A}$ , $I_B = -20\text{mA}$ $I_C = -3.0\text{A}$ , $I_B = -300\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	-935	-1,000	mV	$I_C = -3.0\text{A}$ , $I_B = -300\text{mA}$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	—	-855	-950	mV	$I_C = -3.0\text{A}$ , $V_{CE} = -2\text{V}$
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Output Capacitance	$C_{obo}$	—	17	25	pF	$V_{CB} = -10\text{V}$ , $f = 1.0\text{MHz}$
Current Gain-Bandwidth Product	$f_T$	—	270	—	MHz	$V_{CE} = -10\text{V}$ , $I_C = -50\text{mA}$ , $f = 100\text{MHz}$
Delay Time	$t_d$	—	57	—	ns	$V_{CC} = -10\text{V}$ , $I_C = -1\text{A}$ , $I_{B1} = I_{B2} = -10\text{mA}$
Rise Time	$t_r$	—	69	—	ns	
Storage Time	$t_s$	—	154	—	ns	
Fall Time	$t_f$	—	60	—	ns	

Note: 14. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

**Typical Electrical Characteristics – Q1 (NPN Transistor)** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



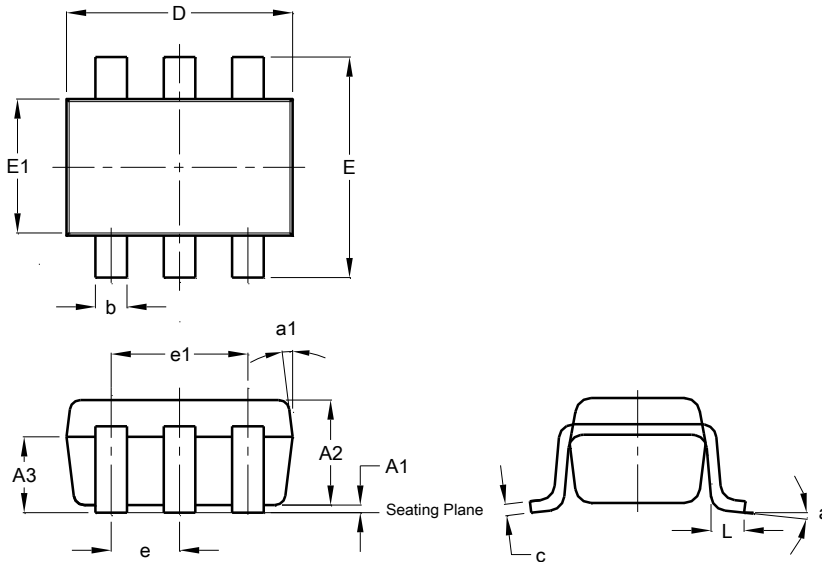
**Typical Electrical Characteristics – Q2 (PNP Transistor)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)



**Package Outline Dimensions**

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

**SOT26**

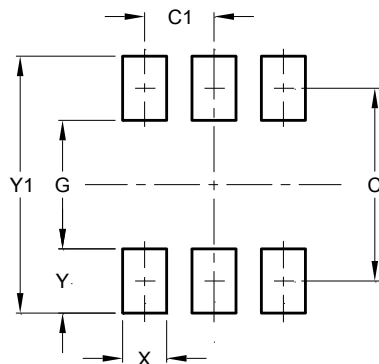


SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

**SOT26**



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20



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